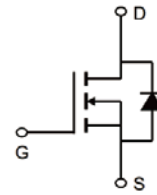




General Features

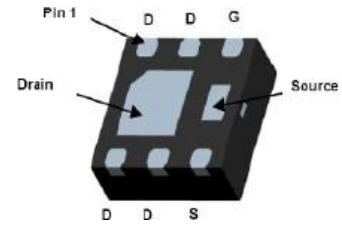
- 20V, 12A
 $R_{DS(ON)} < 22m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} < 28m\Omega @ V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent RDS(ON) and Low Gate Charge
- Lead Free



Equivalent Circuit

Applications

- Load Switch
- PWM Application
- Power Management



DFN2X2-6L

Ordering information

Product ID	Pack	Naming rule	Marking	Qty(PCS)
WLQ2408	DFN2X2-6L	<div style="border: 1px solid black; padding: 5px; display: inline-block;"> WLQ2408 </div> <small>产品名称 product name</small>	2408	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±8	V
I _D @T _A =25°C	Continuous Drain Current	12	A
I _D @T _A =100°C		6	A
I _{DM}	Pulsed Drain Current ¹	30	A
E _{AS}	Single Pulsed Avalanche Energy ²	30	mJ
P _D @T _A =25°C	Power Dissipation	2.7	W
R _{θJA}	Thermal Resistance Junction-ambient ³	46	°C/W
T _J , T _{STG}	Junction & Storage Temperature Range	-55 to 150	°C



Electrical Characteristics (TA=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =20V, V _{GS} =0V	---	---	1.0	uA
I _{GSS}	Gate-Source Leakage Current	V _{DS} =0V, V _{GS} =±8V	---	---	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	0.5	0.75	1.0	V
R _{DS(ON)}	Static Drain-Source On-Resistance ⁴	V _{GS} =4.5V, I _D =10A	---	13	22	mΩ
		V _{GS} =2.5V, I _D =5A	---	18	28	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz	---	665	---	pF
C _{oss}	Output Capacitance		---	90	---	
C _{rss}	Reverse Transfer Capacitance		---	80	---	
Q _g	Total Gate Charge	V _{GS} =0 to 4.5V V _{DD} =10V, I _D =5A	---	13	---	nC
Q _{gs}	Gate-Source Charge		---	2	---	
Q _{gd}	Gate Drain("Miller") Charge		---	3	---	
Switching Characteristics						
T _{d(on)}	Turn-On Delay Time	V _{GS} =4.5V, V _{DD} =10V I _D =5A, R _{GEN} =3W	---	7	---	ns
T _r	Rise Time		---	25	---	
T _{d(off)}	Turn-Off Delay Time		---	34	---	
T _f	Fall Time		---	13	---	
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		---	---	12	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		---	---	30	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =10A	---	---	1.2	V
t _{rr}	Body Diode Reverse Recovery Time	I _F =5A, di/dt=100A/us	---	10	---	ns
Q _{rr}	Body Diode Reverse Recovery Charge		---	2.7	---	nC

Note :

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25°C, V_{DD}=10V, V_G=10V, R_G=25ohm, L=0.5mH, I_{AS}=11A.
3. R_{θJA} is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.



Typical Characteristics

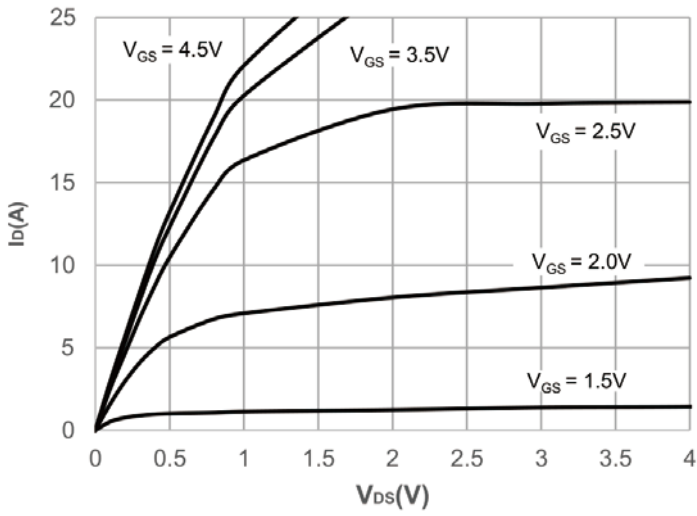


Figure 1: Output Characteristics

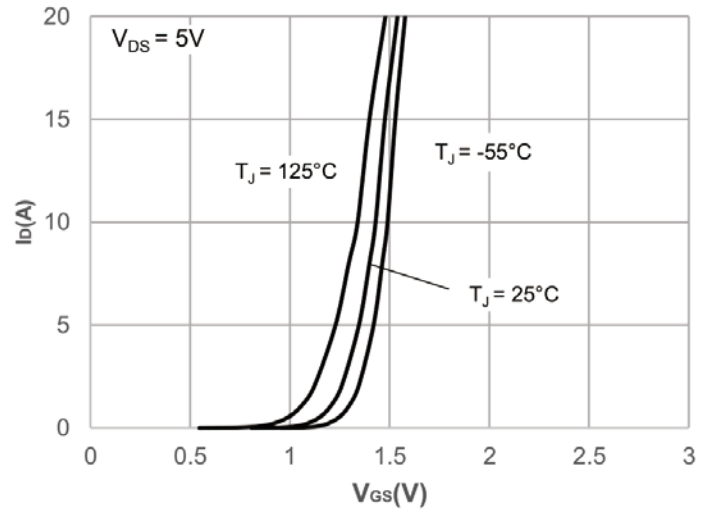


Figure 2: Typical Transfer Characteristics

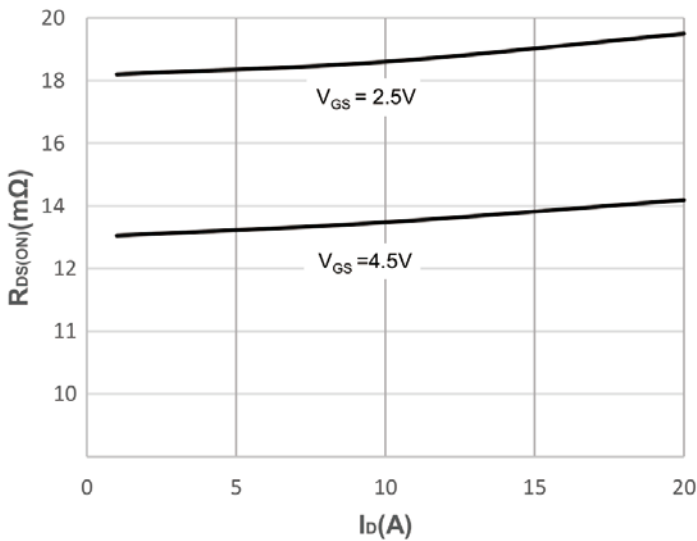


Figure 3: On-resistance vs. Drain Current

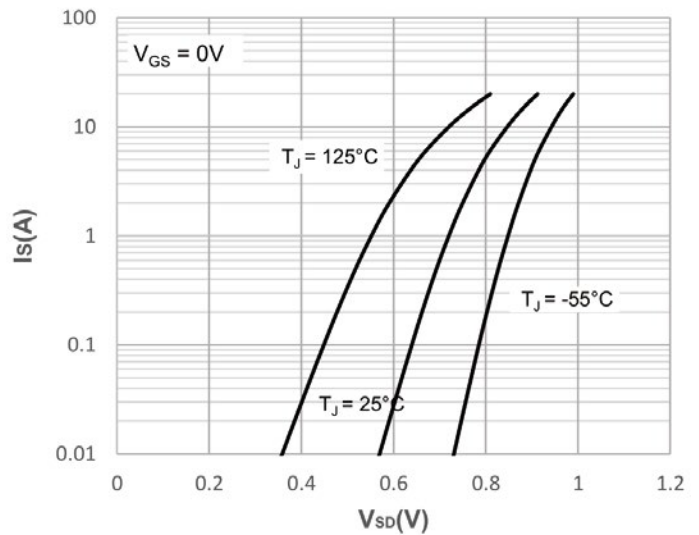


Figure 4: Body Diode Characteristics

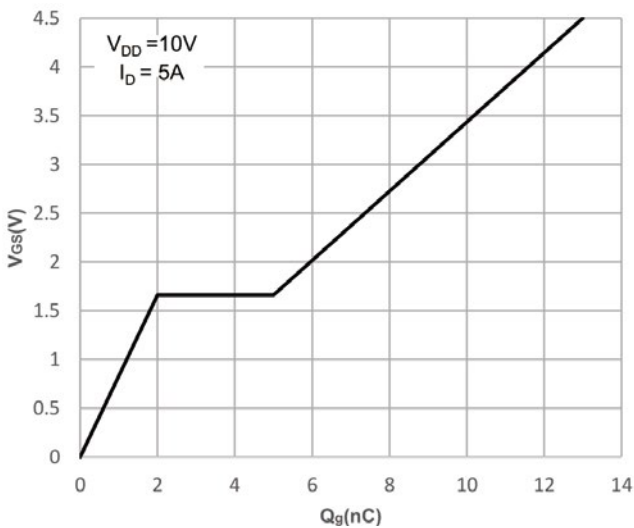


Figure 5: Gate Charge Characteristics

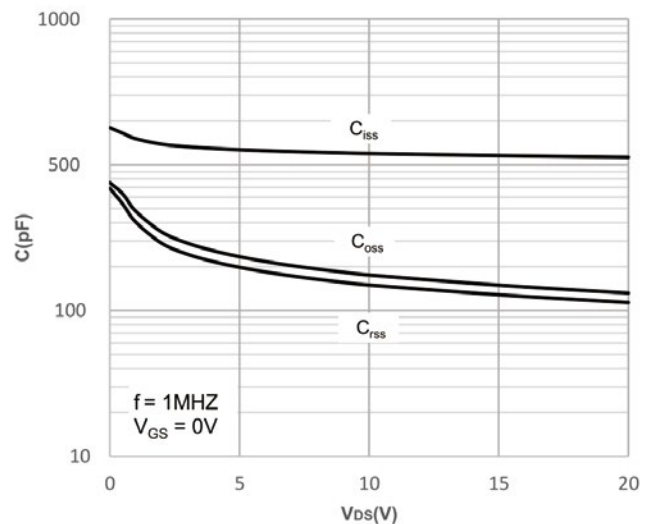


Figure 6: Capacitance Characteristics



Typical Characteristics

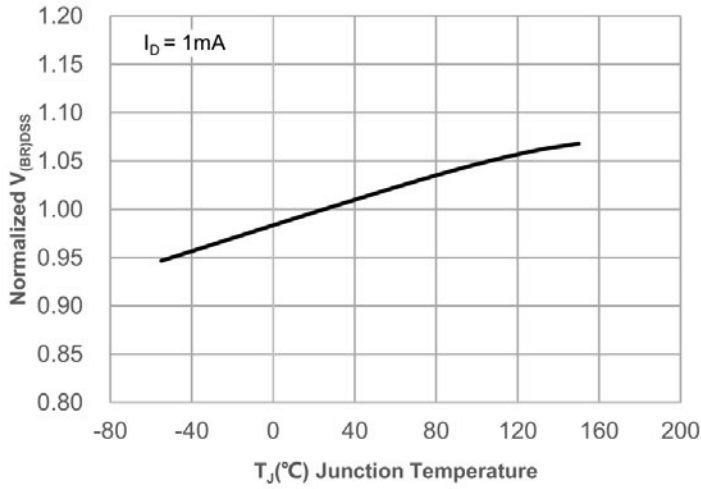


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

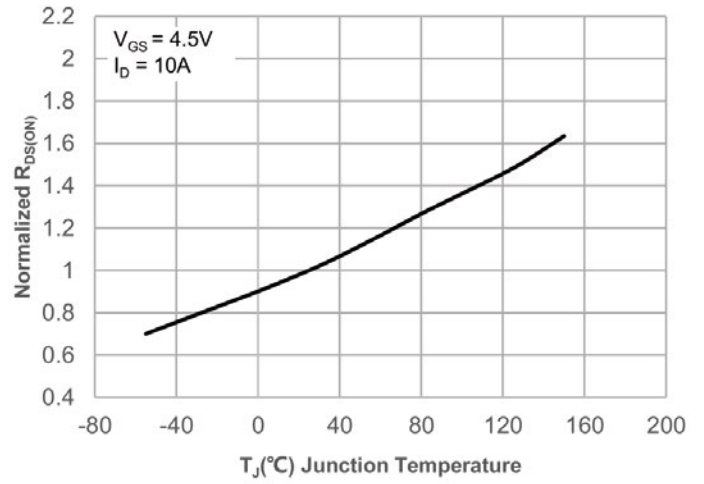


Figure 8: Normalized on Resistance vs. Junction Temperature

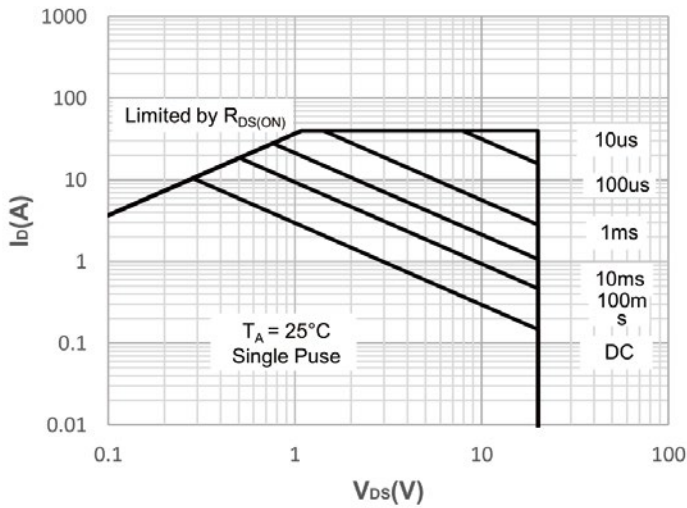


Figure 9: Maximum Safe Operating Area

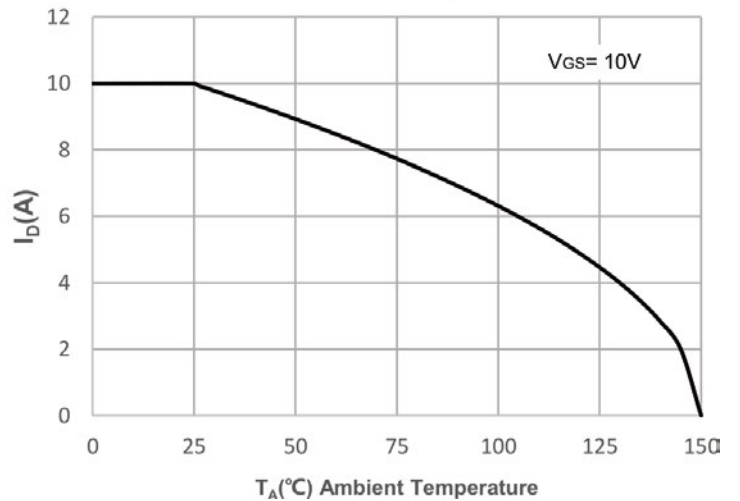


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

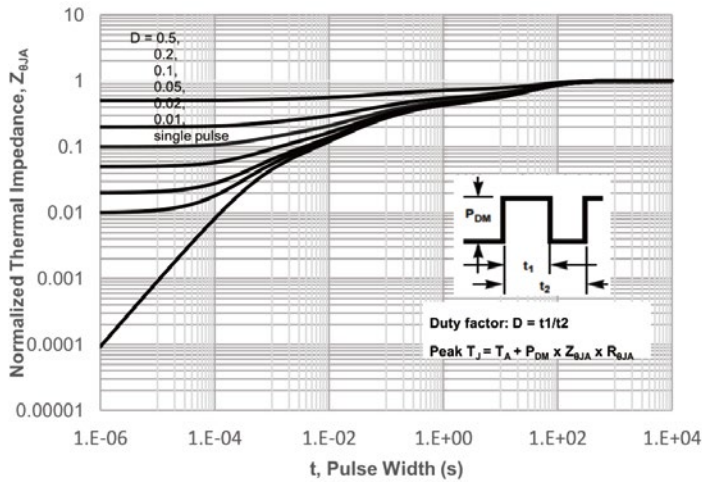


Figure 11: Normalized Maximum Transient Thermal Impedance

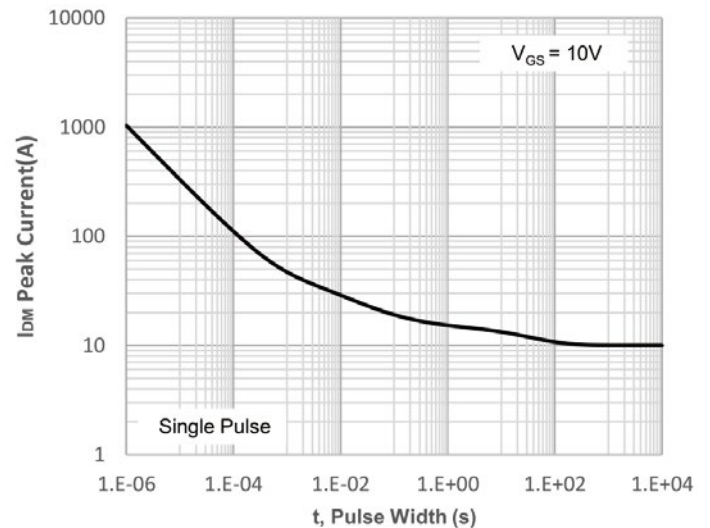
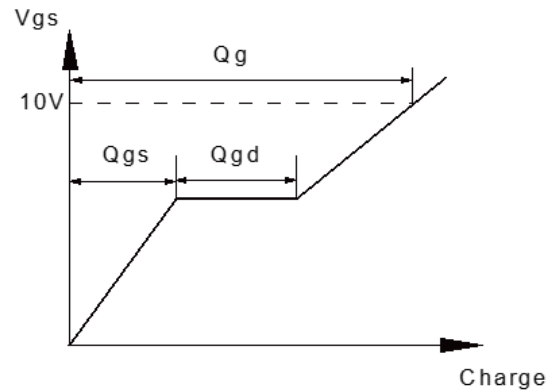
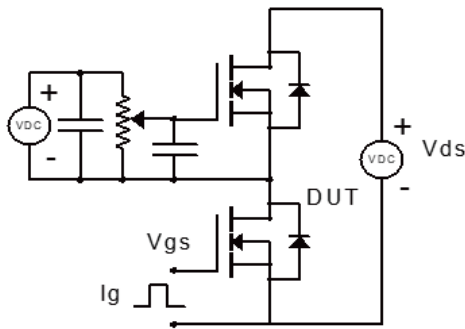


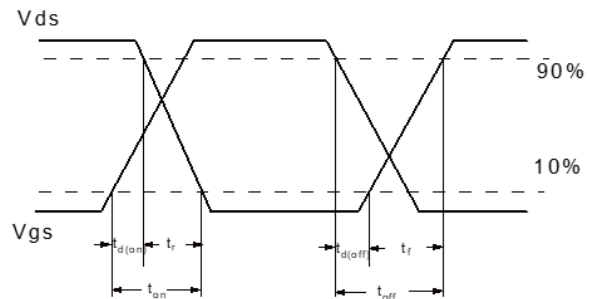
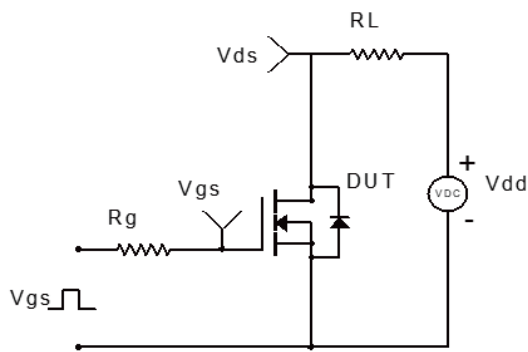
Figure 9: Maximum Safe Operating Area



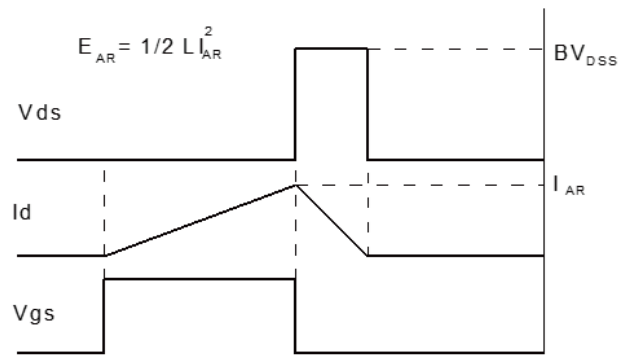
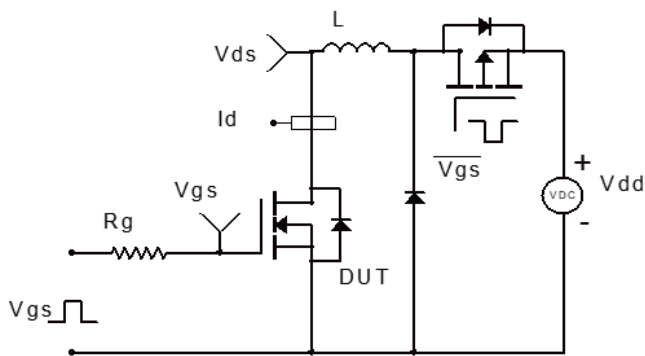
Test Circuit



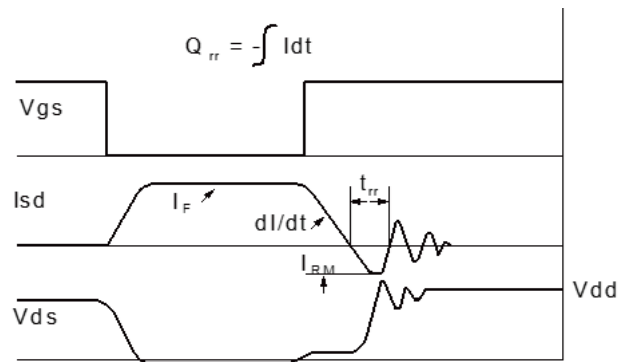
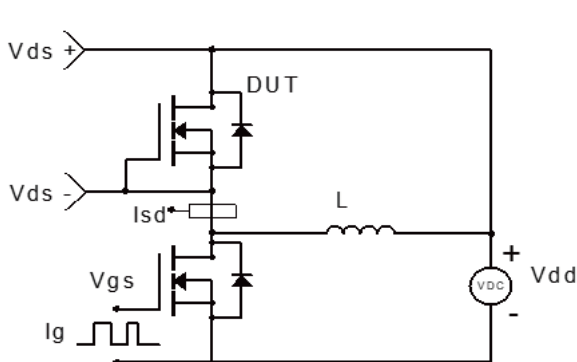
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



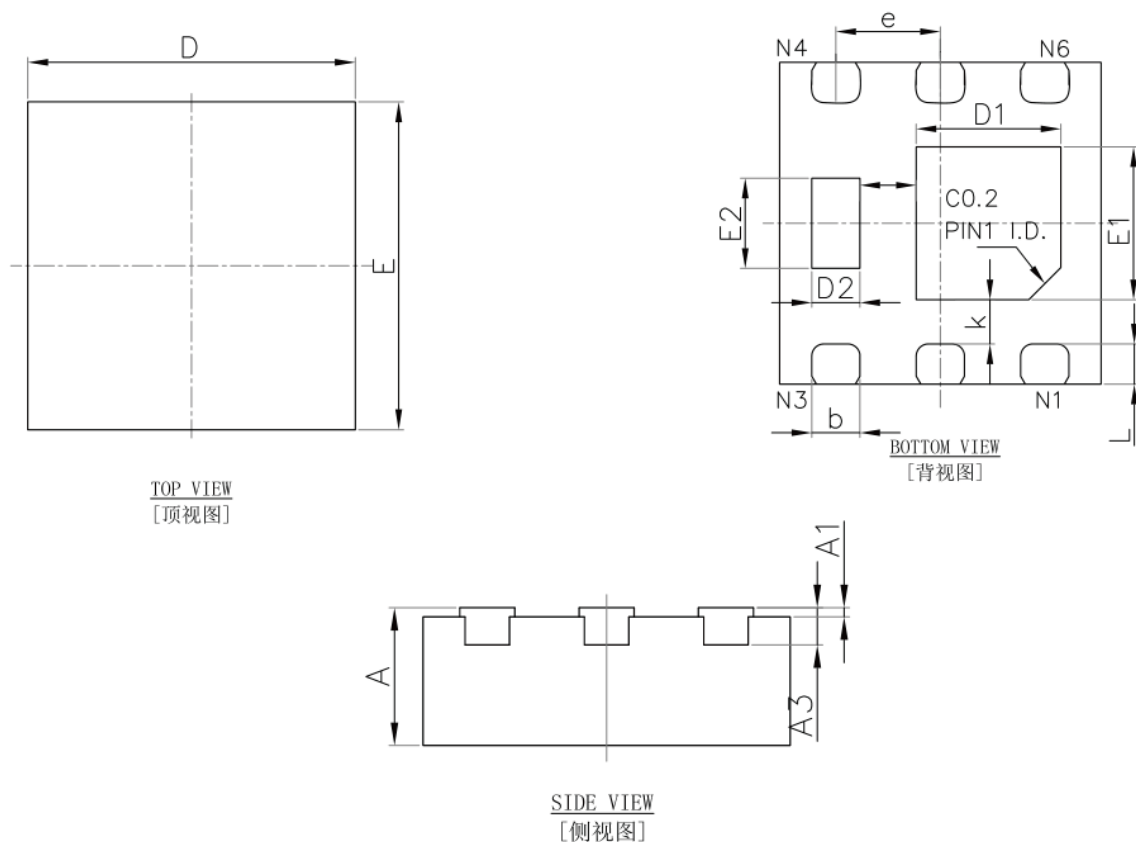
Unclamped inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



DFN2X2-6L Package Outline Dimensions



Symbol	Dimensions in Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.032
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
b	0.250	0.350	0.010	0.014
e	0.650BSC.		0.026BSC.	
k	0.275REF.		0.011REF.	
k1	0.350REF.		0.014REF.	
L	0.174	0.326	0.007	0.013



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